

DS64EV400

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#### SNLS281H-AUGUST 2007-REVISED APRIL 2013

# DS64EV400 Programmable Quad Equalizer

Check for Samples: DS64EV400

### **FEATURES**

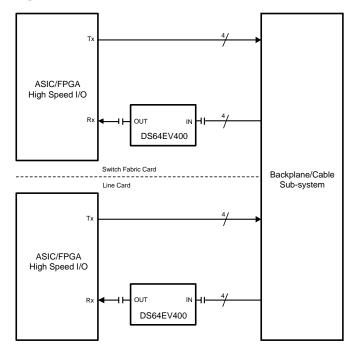
- Equalizes up to 24 dB Loss at 10 Gbps
- Equalizes up to 22 dB Loss at 6.4 Gbps
- 8 Levels of Programmable Equalization
- Settable through Control Pins or SMBus Tnterface
- Operates up to 10 Gbps with 30" FR4 Traces
- Operates up to 6.4 Gbps with 40" FR4 Traces
- 0.175 UI Residual Deterministic Jitter at 6.4 Gbps with 40" FR4 Traces
- Single 2.5V or 3.3V Power Supply
- Signal Detect for Individual Channels
- Standby Mode for Individual Channels
- Supports AC or DC-Coupling with Wide Input Common-Mode
- Low Power Consumption: 375 mW Typ at 2.5V
- Small 7 mm x 7 mm 48-Pin WQFN Package
- 9 kV HBM ESD Rating
- -40 to 85°C Operating Temperature Range

### **Simplified Application Diagram**

### DESCRIPTION

The DS64EV400 programmable quad equalizer provides compensation for transmission medium losses and reduces the medium-induced deterministic jitter for four NRZ data channels. The DS64EV400 is optimized for operation up to 10 Gbps for both cables and FR4 traces. Each equalizer channel has eight levels of input equalization that can be programmed by three control pins, or individually through a Serial Management Bus (SMBus) interface.

The equalizer supports both AC and DC-coupled data paths for long run length data patterns such as PRBS-31, and balanced codes such as 8b/10b. The device uses differential current-mode logic (CML) inputs and outputs. The DS64EV400 is available in a 7 mm x 7 mm 48-pin leadless WQFN package. Power is supplied from either a 2.5V or 3.3V supply.



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Pin Descriptions					
Pin Name	Pin No.	I/O, Type <sup>(1)</sup>	Description		
HIGH SPEED	DIFFEREN	TIAL I/O			
IN_0+ IN_0-	1 2	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip $100\Omega$ terminating resistor is connected between IN_0+ and IN_0 Refer to Figure 7.		
IN_1+ IN_1-	4 5	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip $100\Omega$ terminating resistor is connected between IN_1+ and IN_1 Refer to Figure 7.		
IN_2+ IN_2-	8 9	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip $100\Omega$ terminating resistor is connected between IN_2+ and IN_2 Refer to Figure 7.		
IN_3+ IN_3-	11 12	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip $100\Omega$ terminating resistor is connected between IN_3+ and IN_3 Refer to Figure 7.		
OUT_0+ OUT_0–	36 35	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50 $\Omega$ terminating resistor connects OUT_0+ to V_{DD} and OUT_0- to V_{DD}.		
OUT_1+ OUT_1-	33 32	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50 $\Omega$ terminating resistor connects OUT_1+ to V_{DD} and OUT_1- to V_{DD}.		
OUT_2+ OUT_2–	29 28	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50 $\Omega$ terminating resistor connects OUT_2+ to V <sub>DD</sub> and OUT_2- to V <sub>DD</sub> .		
OUT_3+ OUT_3–	26 25	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50 $\Omega$ terminating resistor connects OUT_3+ to V_{DD} and OUT_3- to V_{DD}.		
EQUALIZATIO		DL			
BST_2 BST_1 BST_0	37 14 23	I, LVCMOS	BST_2, BST_1, and BST_0 select the equalizer strength for all EQ channels. BST_2 is internally pulled high. BST_1 and BST_0 are internally pulled low.		
DEVICE CON	FROL	I			
EN0	44	I, LVCMOS	Enable Equalizer Channel 0 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.		
EN1	42	I, LVCMOS	Enable Equalizer Channel 1 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.		
EN2	40	I, LVCMOS	Enable Equalizer Channel 2 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.		
EN3	38	I, LVCMOS	Enable Equalizer Channel 3 input. When held High, normal operation is selected. When held Low, standby mode is selected. EN is internally pulled High.		
FEB	21	I, LVCMOS	Force External Boost. When held high, the equalizer boost setting is controlled by BST_[2:0] pins. When held low, the equalizer boost setting is controlled by SMBus (Table 1) register bits. FEB is internally pulled High.		
SD0	45	O, LVCMOS	Equalizer Ch0 Signal Detect Output. Produces a High when signal is detected.		
SD1	43	O, LVCMOS	Equalizer Ch1 Signal Detect Output. Produces a High when signal is detected.		
SD2	41	O, LVCMOS	Equalizer Ch2 Signal Detect Output. Produces a High when signal is detected.		
SD3	39	O, LVCMOS	Equalizer Ch3 Signal Detect Output. Produces a High when signal is detected.		
POWER	1	1	·		
V <sub>DD</sub>	3, 6, 7, 10, 13, 15, 46	Power	$V_{DD} = 2.5V \pm 5\%$ or $3.3V \pm 10\%$ . $V_{DD}$ pins should be tied to $V_{DD}$ plane through low inductance path. A 0.01µF bypass capacitor should be connected between each $V_{DD}$ pin to GND planes.		
GND	22, 24, 27, 30, 31, 34	Power	Ground reference. GND should be tied to a solid ground plane through a low impedance path.		
DAP	PAD	Power	Ground reference. The exposed pad at the center of the package must be connected to ground plane of the board.		
SERIAL MAN	AGEMENT	BUS (SMBus) IN	ITERFACE CONTROL PINS		
SDA	18	I/O, LVCMOS	Data input/output (bi-directional). Internally pulled high.		
SDC CS	17 16	I, LVCMOS I, LVCMOS	Clock input. Internally pulled high. Chip select. When pulled high, access to the equalizer SMBus registers are enabled. When pulled low, access to the equalizer SMBus registers are disabled. Please refer to "SMBus configuration Registers" section for detail information.		
Other	1	1			
Reserv	19, 20		Reserved. Do not connect.		
	47,48	<u> </u>			

(1) Note: I = Input O = Output



#### **Connection Diagram**

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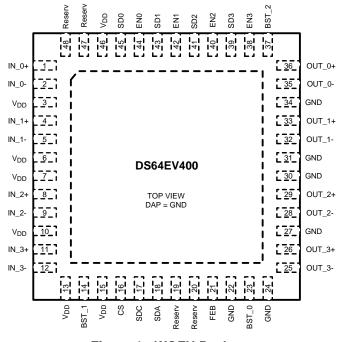


Figure 1. WQFN Package See Package Number NJU0048D

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### Absolute Maximum Ratings <sup>(1)(2)</sup>

Supply Voltage (V <sub>DD</sub> )	-0.5V to +4.0V
CMOS Input Voltage	-0.5V + 4.0V
CMOS Output Voltage	-0.5V to 4.0V
CML Input/Output Voltage	-0.5V to 4.0V
Junction Temperature	+150°C
Storage Temperature	−65°C to +150°C
Lead Temperature (Soldering, 4 Seconds)	+260°C
ESD Rating	
HBM, 1.5 kΩ, 100 pF	> 9 kV
EIAJ, 0Ω, 200 pF	> 250V
Thermal Resistance $\theta_{JA}$ , No Airflow	30°C/W

(1) "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. Absolute Maximum Numbers are ensured for a junction temperature range of -40°C to +125°C. Models are validated to Maximum Operating Voltages only.

(2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

ISTRUMENTS

EXAS

### **Recommended Operating Conditions**

		Min	Тур	Max	Units
Supply Voltage	V <sub>DD2.5</sub> to GND	2.375	2.5	2.625	V
	V <sub>DD3.3</sub> to GND	3.0	3.3	3.6	V
Ambient Temperature		-40	25	+85	°C

### **Electrical Characteristics**

Over recommended operating supply and temperature ranges with default register settings unless other specified.

Parameter	Test Conditions	Min	Тур <sup>(1)</sup>	Max	Units
			1	1	
Power Supply Consumption	Device Output Enabled (EN [0–3] = High), V <sub>DD3.3</sub> <sup>(2)</sup>		490	700	mW
	Device Output Disable (EN [0–3] = Low), V <sub>DD3.3</sub>			100	mW
Power Supply Consumption	Device Output Enabled (EN $[0-3] = High$ ), $V_{DD2.5}$ <sup>(2)</sup>		360	490	mW
	Device Output Disable (EN $[0-3] = Low$ ), $V_{DD2.5}$ <sup>(2)</sup>		30		
Supply Noise Tolerance <sup>(3)</sup>	50 Hz — 100 Hz 100 Hz — 10 MHz 10 MHz — 1.6 GHz		100 40 10		mV <sub>P-P</sub> mV <sub>P-P</sub> mV <sub>P-P</sub>
DC SPECIFICATIONS					
High Level Input Voltage	V <sub>DD3.3</sub>	2.0		V <sub>DD3.3</sub>	V
	V <sub>DD2.5</sub>	1.6		$V_{DD2.5}$	V
Low Level Input Voltage		-0.3		0.8	V
High Level Output Voltage	I <sub>OH</sub> = -3mA, V <sub>DD3.3</sub>	2.4			V
	$I_{OH} = -3mA, V_{DD2.5}$	2.0			
Low Level Output Voltage	I <sub>OL</sub> = 3mA			0.4	V
Input Leakage Current	$V_{IN} = V_{DD}$			+15	μA
	V <sub>IN</sub> = GND	-15			μA
Input Leakage Current with Internal	$V_{IN} = V_{DD}$ , with internal pull-down resistors			+120	μA
Pull-Down/Up Resistors	V <sub>IN</sub> = GND, with internal pull-up resistors	-20			μA
ETECT		·			
Signal Detect ON Threshold Level	Default input signal level to assert SD pin, 6.4 Gbps		70		mV <sub>p-p</sub>
Signal Detect OFF Threshold Level	Default input signal level to de-assert SD, 6.4 Gbps		40		mV <sub>p-p</sub>
EIVER INPUTS (IN_n+, IN_n-)					
Source Transmit Launch Signal Level (IN diff)	AC-Coupled or DC-Coupled Requirement, Differential measurement at point A. Figure 2	400		1600	mV <sub>P-P</sub>
Input Threshold Voltage	Differential measurement at point B. Figure 2		120		mV <sub>P-P</sub>
Supply Voltage of Transmitter to EQ	DC-Coupled Requirement <sup>(4)</sup>	1.6		V <sub>DD</sub>	V
Input Common Mode Voltage	DC-Coupled Requirement, Differential measurement at point A. Figure 2, <sup>(5)</sup>	V <sub>DDTX</sub> – 0.8		V <sub>DDTX</sub> - 0.2	V
Differential Input Return Loss	100 MHz – 3.2 GHz, with fixture's effect de- embedded		10		dB
	Power Supply Consumption         Power Supply Consumption         Supply Noise Tolerance <sup>(3)</sup> DC SPECIFICATIONS         High Level Input Voltage         Low Level Input Voltage         High Level Output Voltage         Input Leakage Current         Input Leakage Current with Internal Pull-Down/Up Resistors         PETECT         Signal Detect ON Threshold Level         Signal Detect OFF Threshold Level         EIVER INPUTS (IN_n+, IN_n-)         Source Transmit Launch Signal Level (IN diff)         Input Threshold Voltage         Supply Voltage of Transmitter to EQ Input Common Mode Voltage	Power Supply Consumption         Device Output Enabled (EN $[0-3] = High)$ , $V_{DD3,3}$ <sup>(2)</sup> Device Output Disable (EN $[0-3] = Low)$ , $V_{DD3,3}$ Power Supply Consumption         Device Output Enabled (EN $[0-3] = High)$ , $V_{DD2,5}$ <sup>(2)</sup> Device Output Disable (EN $[0-3] = Low)$ , $V_{DD2,5}$ <sup>(2)</sup> Supply Noise Tolerance <sup>(3)</sup> 50 Hz — 100 Hz 100 Hz — 10 MHz 100 Hz — 16 GHz           DC SPECIFICATIONS           High Level Input Voltage $V_{DD2,5}$ Low Level Input Voltage $I_{OH} = -3mA$ , $V_{DD2,5}$ Low Level Output Voltage $I_{OH} = -3mA$ , $V_{DD2,5}$ Low Level Output Voltage $I_{OL} = 3mA$ Input Leakage Current $V_{IN} = V_{DD}$ $V_{IN} = GND$ $V_{IN} = GND$ Input Leakage Current with Internal Pull-Down/Up Resistors         Default input signal level to assert SD pin, 6.4 Gbps           Signal Detect OFF Threshold Level         Default input signal level to de-assert SD, 6.4 Gbps           Signal Detect OFF Threshold Level         Default input signal level to de-assert SD, 6.4 Gbps           EIVER INPUTS (IN_n+, IN_n-)         AC-Coupled or DC-Coupled Requirement, Differential measurement at point A. Figure 2           Input Threshold Voltage         DC-Coupled Requirement, Differential measurement at point A. Figure 2           Supply Voltage of Transmitter to EQ DC-Coupled Re	Power Supply ConsumptionDevice Output Enabled (EN [0–3] = High), $V_{DD3,3}(2^{0})$ Device Output Enabled (EN [0–3] = Low), $V_{DD3,3}$ Power Supply ConsumptionDevice Output Enabled (EN [0–3] = High), $V_{DD2,5}(2^{0})$ Device Output Enabled (EN [0–3] = Low), $V_{DD2,5}(2^{0})$ Supply Noise Tolerance (3)50 Hz — 100 Hz 100 Hz — 10 MHz 10 MHz — 1.6 GHzDC SPECIFICATIONSVDD3.3 VDD2.5High Level Input Voltage $V_{DD3.3}$ VDD2.5High Level Output Voltage $I_{OH} = -3mA, V_{DD3.3}$ IOH = $-3mA, V_{DD2.5}$ Low Level Output Voltage $I_{OH} = -3mA, V_{DD2.5}$ IOH = $-3mA, V_{DD2.5}$ Input Leakage Current $V_{IN} = V_{DD}$ VIN = GNDPull-Down/Up Resistors $-20$ VIN = GNDETECTSignal Detect OFF Threshold Level Signal Detect OFF Threshold LevelDefault input signal level to assert SD pin, 6.4 GbpsSource Transmit Launch Signal Level (IN diff)Source Transmit Launch Signal Level Output Threshold VoltageInput Threshold VoltageDefault input signal level to de-assert SD, 6.4 GbpsSupply Voltage of Transmitter to EQ Input Threshold VoltageDef-Coupled Requirement, Differential measurement at point B. Figure 2Supply Voltage of Transmitter to EQ DC-Coupled Requirement, Cifferential measurement at point A. Figure 2, 0 0.8Differential Input Centure Node VoltageDifferential measurement 4 point B. Figure 2, 0Supply Voltage of Transmitter to EQ 0.6-Coupled Requirement, Cifferential measurement at point A. Figure 2, 0Supply Voltage of Transmitter to EQ 0.7-Coupled	Power Supply Consumption         Device Output Enabled (EN [0-3] = High), $V_{DD3,3}(2)$ 490           Power Supply Consumption         Device Output Disable (EN [0-3] = Low), $V_{DD2,5}(2)$ 360           Power Supply Consumption         Device Output Disable (EN [0-3] = High), $V_{DD2,5}(2)$ 30           Supply Noise Tolerance <sup>(3)</sup> 50 Hz - 100 Hz 100 Hz - 10 MHz 100 Hz - 10 GHz         100           DC SPECIFICATIONS         100         40         100           DC SPECIFICATIONS         VDD3.3         2.0         40           High Level Input Voltage         VDD3.3         2.0         40           Input Leakage Current         VDD3.3         2.0         40           Input Leakage Current         VDD2.5         1.6         100           Input Leakage Current with Internal Pull-Down/Up Resistors         V_IN = VDD         -15         10           VIN = GND         -15         VIN = GND         -15         10           Signal Detect OF Threshold Level         Default input signal level to assert SD pin, 6.4 Gbps         70         70           Signal Detect OF Threshold Level         Default input signal level to de-assert SD, 6.4 Gbps         400         120           Input Threshold Voltage         Differential measurement at point A. Figure 2         120         120 <td>Power Supply ConsumptionDevice Output Enabled (EN [0-3] = High), <math>V_{D03,3}^{(2)}</math>490700Power Supply ConsumptionDevice Output Disable (EN [0-3] = Low), <math>V_{D03,3}^{(2)}</math>360490Power Supply ConsumptionDevice Output Enabled (EN [0-3] = High), <math>V_{D02,2}^{(2)}</math>360490Supply Noise Tolerance (3)50 Hz - 100 Hz 100 Hz - 100 Hz 100 Hz - 100 Hz 100 Hz - 100 Hz 100 Hz - 130 Hz100 40DC SPECIFICATIONSVDD2,51.6VDD2,5High Level Input VoltageVDD3,3 VDD2,52.0VDD3,3 0.3High Level Output VoltageI_0H = -3mA, VDD3,3 I_0H = -3mA, VDD2,52.00.4Input Leakage CurrentV_IN = GND VIN = GND-15+120Input Leakage CurrentV_IN = GND VIN = GND-15+120VIN = GND VIN = GND-15-16VDD VIN = GND+15ETECTSignal Detect OFF Threshold LevelDefault input signal level to assert SD pin, 6.4 Gbps701600 GbpsEVER INPUTS (IN_n+, IN_n)AC-Coupled or DC-Coupled Requirement, (IN diff)AC-Coupled or DC-Coupled Requirement, Figure 24001600Input Threshold VoltageDifferential measurement at point A. Figure 2A0016001600Input Threshold VoltageDifferential measurement at point A. Figure 2120YDD YDD-0.2Differential Input Threshold VoltageDifferential measurement at point A. Figure 2100 MHz - 3.2 GHz, with fixture's effect de- YDDYDD YDD-0.2Input Threshold Vol</td>	Power Supply ConsumptionDevice Output Enabled (EN [0-3] = High), $V_{D03,3}^{(2)}$ 490700Power Supply ConsumptionDevice Output Disable (EN [0-3] = Low), $V_{D03,3}^{(2)}$ 360490Power Supply ConsumptionDevice Output Enabled (EN [0-3] = High), $V_{D02,2}^{(2)}$ 360490Supply Noise Tolerance (3)50 Hz - 100 Hz 100 Hz - 100 Hz 100 Hz - 100 Hz 100 Hz - 100 Hz 100 Hz - 130 Hz100 40DC SPECIFICATIONSVDD2,51.6VDD2,5High Level Input VoltageVDD3,3 VDD2,52.0VDD3,3 0.3High Level Output VoltageI_0H = -3mA, VDD3,3 I_0H = -3mA, VDD2,52.00.4Input Leakage CurrentV_IN = GND VIN = GND-15+120Input Leakage CurrentV_IN = GND VIN = GND-15+120VIN = GND VIN = GND-15-16VDD VIN = GND+15ETECTSignal Detect OFF Threshold LevelDefault input signal level to assert SD pin, 6.4 Gbps701600 GbpsEVER INPUTS (IN_n+, IN_n)AC-Coupled or DC-Coupled Requirement, (IN diff)AC-Coupled or DC-Coupled Requirement, Figure 24001600Input Threshold VoltageDifferential measurement at point A. Figure 2A0016001600Input Threshold VoltageDifferential measurement at point A. Figure 2120YDD YDD-0.2Differential Input Threshold VoltageDifferential measurement at point A. Figure 2100 MHz - 3.2 GHz, with fixture's effect de- YDDYDD YDD-0.2Input Threshold Vol

(1) Typical values represent most likely parametric norms at  $V_{DD}$  = 3.3V or 2.5V,  $T_A$  = 25°C, and at the Recommended Operation Conditions at the time of product characterization and are not ensured.

The V<sub>DD2.5</sub> is V<sub>DD</sub> =  $2.5V \pm 5\%$  and V<sub>DD3.3</sub> is V<sub>DD</sub> =  $3.3V \pm 10\%$ . Allowed supply noise (mV<sub>P-P</sub> sine wave) under typical conditions. (2)

- (3)
- Recommended value. Parameter not tested in production. (4)

Measured with clock-like {11111 00000} pattern. (5)

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#### **Electrical Characteristics (continued)**

Over recommended operating supply and temperature ranges with default register settings unless other specified.

Parameter		Test Conditions	Min	Тур <sup>(1)</sup>	Max	Units
R <sub>IN</sub>	Input Resistance	Differential across IN+ and IN-, Figure 7	85	100	115	Ω
	PUTS (OUT_n+, OUT_n-)			4		
V <sub>OD</sub>	Output Differential Voltage Level (OUT diff)	Differential measurement with OUT+ and OUT- terminated by $50\Omega$ to GND, AC-Coupled Figure 3	500	620	725	mV <sub>P-P</sub>
V <sub>OCM</sub>	Output Common Mode Voltage	Single-ended measurement DC-Coupled with 50 $\Omega$ terminations $^{(5)}$	V <sub>DD</sub> - 0.2		V <sub>DD</sub> - 0.1	V
t <sub>R</sub> , t <sub>F</sub>	Transition Time	20% to 80% of differential output voltage, measured within 1" from output pins. Figure 3, <sup>(5)</sup>	20		60	ps
R <sub>O</sub>	Output Resistance	Single ended to V <sub>DD</sub>	42	50	58	Ω
R <sub>LO</sub>	Differential Output Return Loss	100 MHz – 1.6 GHz, with fixture's effect de- embedded. IN+ = static high.		10		dB
t <sub>PLHD</sub>	Differential Low to High Propagation Delay	Propagation delay measurement at 50% VO between input to output, 100 Mbps. Figure 4,		240		ps
t <sub>PHLD</sub>	Differential High to Low Propagation Delay	(5)		240		ps
t <sub>CCSK</sub>	Inter Pair Channel to Channel Skew	Difference in 50% crossing between channels		7		ps
t <sub>PPSK</sub>	Part to Part Output Skew	Difference in 50% crossing between outputs		20		ps
EQUALIZ	ATION	•		-i		•
DJ1	Residual Deterministic Jitter at 10 Gbps	30" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 <sup>7</sup> -1) pattern. <sup>(6)</sup>		0.20		UI <sub>P-P</sub>
DJ2	Residual Deterministic Jitter at 6.4 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 <sup>7</sup> -1) pattern. <sup>(7)(6)</sup>		0.17	0.26	UI <sub>P-P</sub>
DJ3	Residual Deterministic Jitter at 5 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x07, PRBS-7 (2 <sup>7</sup> -1) pattern. <sup>(7) (6)</sup>		0.12	0.20	UI <sub>P-P</sub>
DJ4	Residual Deterministic Jitter at 2.5 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x07, PRBS-7 (2 <sup>7</sup> -1) pattern. <sup>(7)(6)</sup>		0.1	0.16	UI <sub>P-P</sub>
RJ	Random Jitter	See <sup>(8)(9)</sup>		0.5		psrms
SIGNAL D	DETECT and ENABLE TIMING					
t <sub>ZISD</sub>	Input OFF to ON detect — SD Output High Response Time	Response time measurement at $V_{IN}$ to SD output, $V_{IN}$ = 800 mV <sub>P-P</sub> , 100 Mbps, 40" of 6 mil		35		ns
t <sub>IZSD</sub>	Input ON to OFF detect — SD Output Low Response Time	microstrip FR4 Figure 2 and Figure 5, <sup>(8)</sup>		400		ns
t <sub>OZOED</sub>	EN High to Output ON Response Time	Response time measurement at EN input to $V_O$ , $V_{IN}$ = 800 m $V_{P-P}$ , 100 Mbps, 40" of 6 mil		150		ns
t <sub>ZOED</sub>	EN Low to Output OFF Response Time	microstrip FR4 Figure 2 and Figure 7, <sup>(8)</sup>		5		ns

(6) Deterministic jitter is measured at the differential outputs (point C of Figure 2), minus the deterministic jitter before the test channel (point A of Figure 2). Random jitter is removed through the use of averaging or similar means. Specification is ensured by characterization at optimal boost setting and is not tested in production.

(7)

Measured with clock-like {11111 00000} pattern. (8)

Random jitter contributed by the equalizer is defined as sqrt  $(J_{OUT}^2 - J_{IN}^2)$ .  $J_{OUT}$  is the random jitter at equalizer outputs in ps-rms, see point C of Figure 2;  $J_{IN}$  is the random jitter at the input of the equalizer in ps-rms, see point B of Figure 2. (9)

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STRUMENTS

EXAS

## **Electrical Characteristics — Serial Management Bus Interface**

Over recommended operating supply and temperature ranges unless other specified.

Parameter		Test Conditions	Min	Тур	Max	Units
SERIAL BUS	S INTERFACE DC SPECIFICATIONS					-
V <sub>IL</sub>	Data, Clock Input Low Voltage				0.8	V
V <sub>IH</sub>	Data, Clock Input High Voltage		2.1		V <sub>DD</sub>	V
I <sub>PULLUP</sub>	Current Through Pull-Up Resistor or Current Source	High Power Specification	4			mA
V <sub>DD</sub>	Nominal Bus Voltage		2.375		3.6	V
I <sub>LEAK-Bus</sub>	Input Leakage Per Bus Segment	See (1)	-200		+200	μA
I <sub>LEAK-Pin</sub>	Input Leakage Per Device Pin			-15		μA
CI	Capacitance for SDA and SDC	See (1)(2)			10	pF
R <sub>TERM</sub>	External Termination Resistance pull	V <sub>DD3.3</sub> , <sup>(1)(2)(3)</sup>		2000		Ω
	to V <sub>DD</sub> = 2.5V ± 5% OR 3.3V ± 10%	V <sub>DD2.5</sub> , <sup>(1)(2)(3)</sup>		1000		Ω
SERIAL BUS	S INTERFACE TIMING SPECIFICATION					
FSMB	Bus Operating Frequency	See <sup>(4)</sup>	10		100	kHz
TBUF	Bus Free Time Between Stop and Start Condition		4.7			μs
THD:STA	Hold time after (Repeated) Start Condition. After this period, the first clock is generated.	At I <sub>PULLUP</sub> , Max	4.0			μs
TSU:STA	Repeated Start Condition Setup Time		4.7			μs
TSU:STO	Stop Condition Setup Time		4.0			μs
THD:DAT	Data Hold Time		300			ns
TSU:DAT	Data Setup Time		250			ns
T <sub>TIMEOUT</sub>	Detect Clock Low Timeout	See (4)	25		35	ms
T <sub>LOW</sub>	Clock Low Period		4.7			μs
T <sub>HIGH</sub>	Clock High Period	See <sup>(4)</sup>	4.0		50	μs
T <sub>LOW</sub> :SEXT	Cumulative Clock Low Extend Time (Slave Device)	See <sup>(4)</sup>			2	ms
t <sub>F</sub>	Clock/Data Fall Time	See <sup>(4)</sup>			300	ns
t <sub>R</sub>	Clock/Data Rise Time	See <sup>(4)</sup>			1000	ns
t <sub>POR</sub>	Time in which a device must be operational after power-on reset	See <sup>(4)</sup>			500	ms

Recommended value. Parameter not tested in production.
 Recommended maximum capacitance load per bus segment is 400pF.

(3) (4) Maximum termination voltage should be identical to the device supply voltage.

Compliant to SMBus 2.0 physical layer specification. See System Management Bus (SMBus) Specification Version 2.0, section 3.1.1 SMBus common AC specifications for details.



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#### System Management Bus (SMBus) and Configuration Registers

The System Management Bus interface is compatible to SMBus 2.0 physical layer specification. The use of the Chip Select signal is **required**. Holding the CS pin High enables the SMBus port allowing access to the configuration registers. Holding the CS pin Low disables the device's SMBus allowing communication from the host to other slave devices on the bus. In the STANDBY state, the System Management Bus remains active. When communication to other devices on the SMBus is active, the CS signal for the DS32EV400s must be driven Low.

The address byte for all DS64EV400s is AC'h. Based on the SMBus 2.0 specification, the DS64EV400 has a 7bit slave address of 1010110'b. The LSB is set to 0'b (for a WRITE), thus the 8-bit value is 1010 1100'b or AC'h.

The SDC and SDA pins are 3.3V LVCMOS signaling and include high-Z internal pull up resistors. External low impedance pull up resistors maybe required depending upon SMBus loading and speed. Note, these pins are not 5V tolerant.

#### Transfer of Data via the SMBus

During normal operation the data on SDA must be stable during the time when SDC is High.

There are three unique states for the SMBus:

**START** A High-to-Low transition on SDA while SDC is High indicates a message START condition.

**STOP** A Low-to-High transition on SDA while SDC is High indicates a message STOP condition.

**IDLE** If SDC and SDA are both High for a time exceeding t<sub>BUF</sub> from the last detected STOP condition or if they are High for a total exceeding the maximum specification for t<sub>HIGH</sub> then the bus will transfer to the IDLE state.

#### **SMBus Transactions**

The device supports WRITE and READ transactions. See Register Description table for register address, type (Read/Write, Read Only), default value and function information.

#### Writing a Register

To write a register, the following protocol is used (see SMBus 2.0 specification).

- 1. The Host (Master) selects the device by driving its SMBus Chip Select (CS) signal High.
- 2. The Host drives a START condition, the 7-bit SMBus address, and a "0" indicating a WRITE.
- 3. The Device (Slave) drives the ACK bit ("0").
- 4. The Host drives the 8-bit Register Address.
- 5. The Device drives an ACK bit ("0").
- 6. The Host drive the 8-bit data byte.
- 7. The Device drives an ACK bit ("0").
- 8. The Host drives a STOP condition.
- 9. The Host de-selects the device by driving its SMBus CS signal Low.

The WRITE transaction is completed, the bus goes IDLE and communication with other SMBus devices may now occur.

#### **Reading a Register**

To read a register, the following protocol is used (see SMBus 2.0 specification).

- 1. The Host (Master) selects the device by driving its SMBus Chip Select (CS) signal High.
- 2. The Host drives a START condition, the 7-bit SMBus address, and a "0" indicating a WRITE.
- 3. The Device (Slave) drives the ACK bit ("0").
- 4. The Host drives the 8-bit Register Address.
- 5. The Device drives an ACK bit ("0").
- 6. The Host drives a START condition.
- 7. The Host drives the 7-bit SMBus Address, and a "1" indicating a READ.
- 8. The Device drives an ACK bit "0".

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9. The Device drives the 8-bit data value (register contents).

- 10. The Host drives a NACK bit "1" indicating end of the READ transfer.
- 11. The Host drives a STOP condition.
- 12. The Host de-selects the device by driving its SMBus CS signal Low.

The READ transaction is completed, the bus goes IDLE and communication with other SMBus devices may now occur.

See Table 1 for more information.

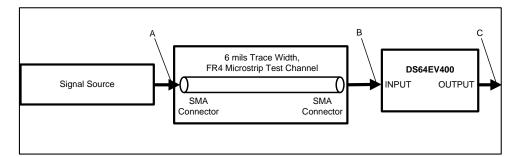
Name	Address	Default	<b>Type</b> (1)	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Status	0x00	0x00	RO	ID Revision	ļ	ļ	ļ	SD3	SD2	SD1	SD0
Status	0x01	0x00	RO	EN1	Boost 1			EN0	Boost 0	1	
Status	0x02	0x00	RO	EN3	Boost 3			EN2	Boost 2		
Enable/Boost (CH 0, 1)	0x03	0x44	RW	EN1 Output 0:Enable 1:Disable	Boost Con 000 (Min E 001 010 011 100 (Defat 101 110 111 (Max	ult)		EN0 Output 0:Enable 1:Disable	Boost Cor 000 (Min I 010 011 100 (Defa 101 110 111 (Max	, ult)	10
Enable/Boost (CH 2, 3)	0x04	0x44	RW	EN3 Output 0:Enable 1:Disable	Boost Con 000 (Min E 001 010 011 100 (Defat 101 110 111 (Max	ult)	3	EN2 Output 0:Enable 1:Disable	Boost Cor 000 (Min I 010 011 100 (Defa 101 110 111 (Max	Boost) ult)	12
Signal Detect	0x05	0x00	RW	SD3 ON Thre Select 00: 70 mV (D 01: 55 mV 10: 90 mV 11: 75 mV		SD2 ON T Select 00: 70 mV 01: 55 mV 10: 90 mV 11: 75 mV	(Default)	SD1 ON Th Select 00: 70 mV ( 01: 55 mV 10: 90 mV 11: 75 mV		Select	١V
Signal Detect	0x06	0x00	RW	III. 75 mV         III. 75 mV           SD3 OFF Threshold         SD2 OFF Threshold           Select         Select           00: 40 mV (Default)         00: 40 mV (Default)           01: 30 mV         01: 30 mV           10: 55 mV         10: 55 mV           11: 45 mV         11: 45 mV		SD1 OFF T Select 00: 40 mV ( 01: 30 mV 10: 55 mV 11: 45 mV		Select	١V		
SMBus Control	0x07	0x00	RW	Reserved							SMBus Enable Control 0: Disable 1: Enable
Output Level	0x08	0x78	RW	Reserved				Output Leve 00: 400 mV 01: 540 mV 10: 620 mV P(Default) 11: 760 mV	P-P P-P P-	Reserve	d

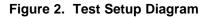
Table 1	1	SMBus	Register	Address
Iable	••	SINDUS	Negister	Audicaa

(1) Note: RO = Read Only, RW = Read/Write



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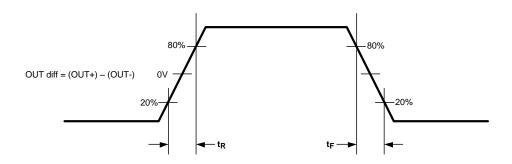


Figure 3. CML Output Transition Times

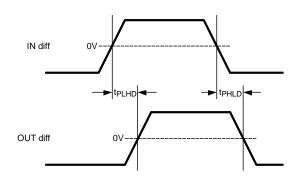


Figure 4. Propagation Delay Timing Diagram

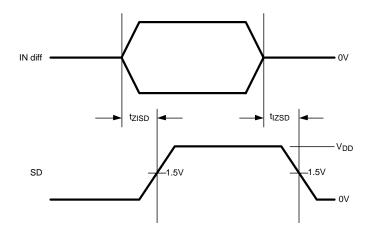
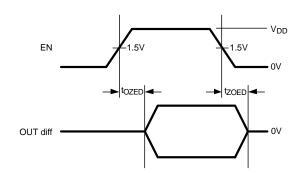
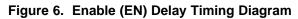


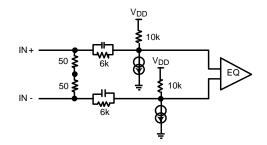
Figure 5. Signal Detect (SD) Delay Timing Diagram



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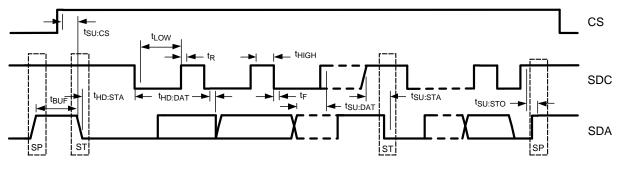


Figure 8. SMBus Timing Parameters

### DS64EV400 FUNCTIONAL DESCRIPTIONS

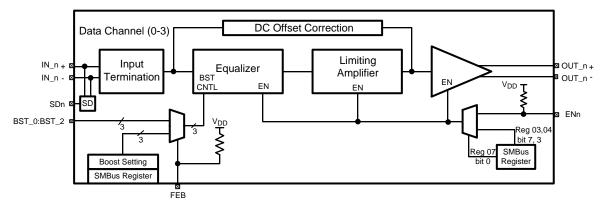
The DS64EV400 is a programmable quad equalizer optimized for operation up to 10 Gbps for backplane and cable applications.

### DATA CHANNELS

The DS64EV400 provides four data channels. Each data channel consists of an equalizer stage, a limiting amplifier, a DC offset correction block, and a CML driver as shown in Figure 9.



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## EQUALIZER BOOST CONTROL

Each data channel support eight programmable levels of equalization boost. The state of the FEB pin determines how the boost settings are controlled. If the FEB pin is held High, then the equalizer boost setting is controlled by the Boost Set pins (BST\_[2:0]) in accordance with Table 2. If this programming method is chosen, then the boost setting selected on the Boost Set pins is applied to all channels. When the FEB pin is held Low, the equalizer boost level is controlled through the SMBus. This programming method is accessed via the appropriate SMBus registers (see Table 1). Using this approach, equalizer boost settings can be programmed for each channel individually. FEB is internally pulled High (default setting); therefore if left unconnected, the boost settings are controlled by the Boost Set pins (BST\_[0:2]). The eight levels of boost settings enables the DS64EV400 to address a wide range of media loss and data rates.

6 mil Microstrip FR4 Trace Length (m)	24 AWG Twin-AX cable length (m)	Channel Loss at 3.2 GHz (dB)	Channel Loss at 5 GHz (dB)	BST_N [2, 1, 0]
0	0	0	0	000
5	2	5	6	0 0 1
10	3	7.5	10	010
15	4	10	14	011
20	5	12.5	18	1 0 0 (Default)
25	6	15	21	101
30	7	17	24	110
40	10	22	30	111

 Table 2. EQ Boost Control Table

## DEVICE STATE AND ENABLE CONTROL

The DS64EV400 has an enable feature on each data channel which provides the ability to control device power consumption. This feature can be controlled either an Enable Pin (EN\_n) with Reg 07 = 00'h (default value), or by the Enable Control Bit register which can be configured through the SMBus port (see Table 1 and Table 3 for detail register information), which require setting Reg 07 = 01'h and changing register value of Reg 03, 04. If the Enable is activated using either the external EN\_n pin or SMBUS register, the corresponding data channel is placed in the ACTIVE state and all device blocks function as described. The DS64EV400 can also be placed in STANDBY mode to save power. In the STANDBY mode only the control interface including the SMBus port, as well as the signal detection circuit remain active.



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Table 3. Controlling Device State					
Register 07[0] (SMBus)	ENn Pin (CMOS)	CH 0: Reg. 03 bit 3 CH 1: Reg. 03 bit 7 CH 2: Reg. 04 bit 3 CH 3: Reg. 04 bit 7 (EN Control)	Device State		
0 : Disable	1	Х	ACTIVE		
0 : Disable	0	Х	STANDBY		
1 : Enable	X	0	ACTIVE		
1 : Enable	X	1	STANDBY		

## SIGNAL DETECT

The DS64EV400 features a signal detect circuit on each data channel. The status of the signal of each channel can be determined by either reading the Signal Detect bit (SDn) in the SMBus registers (see Table 1) or by the state of each SDn pin. An output logic high indicates the presence of a signal that has exceeded the ON threshold value (called SD\_ON). An output logic Low means that the input signal has fallen below the OFF threshold value (called SD\_OFF). These values are programmed via the SMBus (Table 1). If not programmed via the SMBus, the thresholds take on the default values as shown in Table 4. The Signal Detect threshold values can be changed through the SMBus. All threshold values specified are DC peak-to-peak differential signals (positive signal minus negative signal) at the input of the device.

#### Table 4. Signal Detect Threshold Values

Channel 0: Bit 1 Channel 1: Bit 3 Channel 2: Bit 5 Channel 3: Bit 7	Channel 0: Bit 0 Channel 1: Bit 2 Channel 2: Bit 4 Channel 3: Bit 6	SD_OFF Threshold Register 06 (mV)	SD_ON Threshold Register 05 (mV)
0	0	40 (Default)	70 (Default)
0	1	30	55
1	0	55	90
1	1	45	75

## OUTPUT LEVEL CONTROL

The output amplitude of the CML drivers for each channel can be controlled via the SMBus (see Table 1). The default output level is 620 mV<sub>p-p</sub>. The following Table presents the output level values supported:

All Channels : Bit 3	All Channels : Bit 2	Output Level Register 08 (mV <sub>P-P</sub> )
0	0	400
0	1	540
1	0	620 (Default)
1	1	760

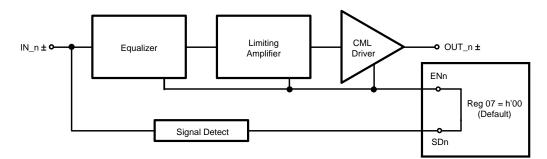
#### Table 5. Output Level Control Settings

### AUTOMATIC ENABLE FEATURE

It may be desirable to place unused channels in power-saving Standby mode. This can be accomplished by connecting the Signal detect (SDn) pin to the Enable (ENn) pin for each channel (See Figure 10). In order for this option to function properly, the register value for Reg. 07 should be 00'h (default value). If an input signal swing applied to a data channel is above the voltage level threshold as shown in Table 4, then the SDn output pin is asserted High. If the SDn pin is connected to the ENn pin, this will enable the equalizer, limiting amplifier, and output buffer on the data channels; thus the DS64EV400 will automatically enter the ACTIVE state. If the input signal swing falls below the SD\_OFF threshold level, then the SDn output will be asserted Low, causing the channel to be placed in the STANDBY state.



#### **DS64EV400** Applications Information





#### UNUSED EQUALIZER CHANNELS

It is recommended to put all unused channels into standby mode.

#### **GENERAL RECOMMENDATIONS**

The DS64EV400 is a high performance circuit capable of delivering excellent performance. Careful attention must be paid to the details associated with high-speed design as well as providing a clean power supply. Refer to the LVDS Owner's Manual for more detailed information on high speed design tips to address signal integrity design issues.

#### PCB LAYOUT CONSIDERATIONS FOR DIFFERENTIAL PAIRS

The CML inputs and outputs must have a controlled differential impedance of  $100\Omega$ . It is preferable to route CML lines exclusively on one layer of the board, particularly for the input traces. The use of vias should be avoided if possible. If vias must be used, they should be used sparingly and must be placed symmetrically for each side of a given differential pair. Route the CML signals away from other signals and noise sources on the printed circuit board. See AN-1187(SNOA401) for additional information on WQFN packages.

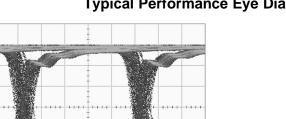
#### POWER SUPPLY BYPASSING

Two approaches are recommended to ensure that the DS64EV400 is provided with an adequate power supply. First, the supply ( $V_{DD}$ ) and ground (GND) pins should be connected to power planes routed on adjacent layers of the printed circuit board. The layer thickness of the dielectric should be minimized so that the  $V_{DD}$  and GND planes create a low inductance supply with distributed capacitance. Second, careful attention to supply bypassing through the proper use of bypass capacitors is required. A  $0.01\mu$ F bypass capacitor should be connected to each  $V_{DD}$  pin such that the capacitor is placed as close as possible to the DS64EV400. Smaller body size capacitors can help facilitate proper component placement. Additionally, three capacitors with capacitance in the range of 2.2  $\mu$ F to 10  $\mu$ F should be incorporated in the power supply bypassing design as well. These capacitors can be either tantalum or an ultra-low ESR ceramic and should be placed as close as possible to the DS64EV400.

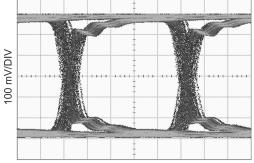
#### DC COUPLING

The DS64EV400 supports both AC coupling with external ac coupling capacitor, and DC coupling to its upstream driver, or downstream receiver. With DC coupling, users must ensure the input signal common mode is within the range of the electrical specification  $V_{ICMDC}$  and the device output is terminated with 50  $\Omega$  to  $V_{DD}$ . When power-up and power-down the device, both the DS64EV400 and the downstream receiver should be power-up and power-down together. This is to avoid the internal ESD structures at the output of the DS64EV400 at power-down from being turned on by the downstream receiver.

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### **Typical Performance Eye Diagrams and Curves**



80 ps/DIV

Figure 11. Equalized Signal (40 In FR4, 2.5Gbps, PRBS7, 0x07 Setting)

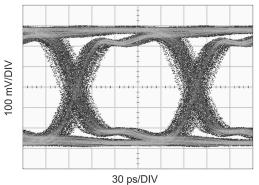


Figure 13. Equalized Signal (40 In FR4, 6.4 Gbps, PRBS7, 0x06 Setting)

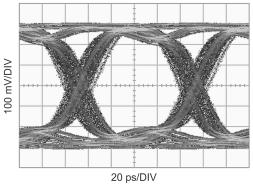
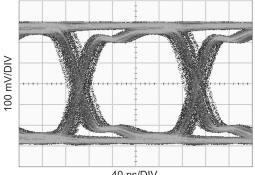


Figure 15. Equalized Signal (30 In FR4, 10 Gbps, PRBS7, 0x06 Setting)



40 ps/DIV

Figure 12. Equalized Signal (40 In FR4, 5Gbps, PRBS7, 0x07 Setting)

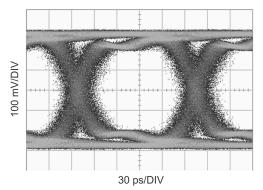


Figure 14. Equalized Signal (40 In FR4, 6.4 Gbps, PRBS31, 0x06 Setting)

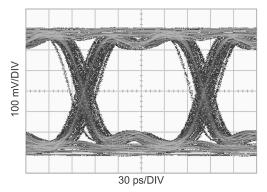


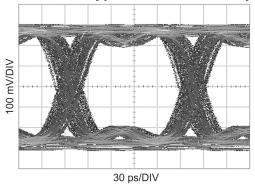
Figure 16. Equalized Signal (10m 24 AWG Twin-Ax Cable, 6.4 Gbps, PRBS7, 0x07 Setting)





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Typical Performance Eye Diagrams and Curves (continued)





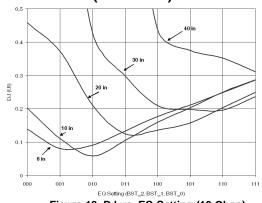
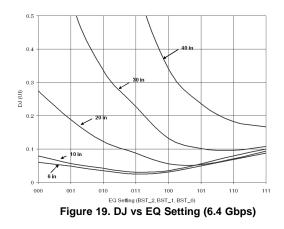


Figure 18. DJ vs. EQ Setting (10 Gbps)



Ch	nanges from Revision G (April 2013) to Revision H	Page
•	Changed layout of National Data Sheet to TI format	15

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15-Apr-2013

## **PACKAGING INFORMATION**

Orderable Devic	e	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
		(1)		Drawing		Qty	(2)		(3)		(4)	
DS64EV400SQ/NC	PB /	ACTIVE	WQFN	NJU	48	250	Green (RoHS & no Sb/Br)	SN	Level-3-260C-168 HR	-40 to 85	DS64EV400	Samples
DS64EV400SQX/NO	OPB /	ACTIVE	WQFN	NJU	48	2500	Green (RoHS & no Sb/Br)	SN	Level-3-260C-168 HR	-40 to 85	DS64EV400	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS64EV400SQ/NOPB	WQFN	NJU	48	250	178.0	16.4	7.3	7.3	1.3	12.0	16.0	Q1
DS64EV400SQX/NOPB	WQFN	NJU	48	2500	330.0	16.4	7.3	7.3	1.3	12.0	16.0	Q1

TEXAS INSTRUMENTS

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# PACKAGE MATERIALS INFORMATION

24-Apr-2013

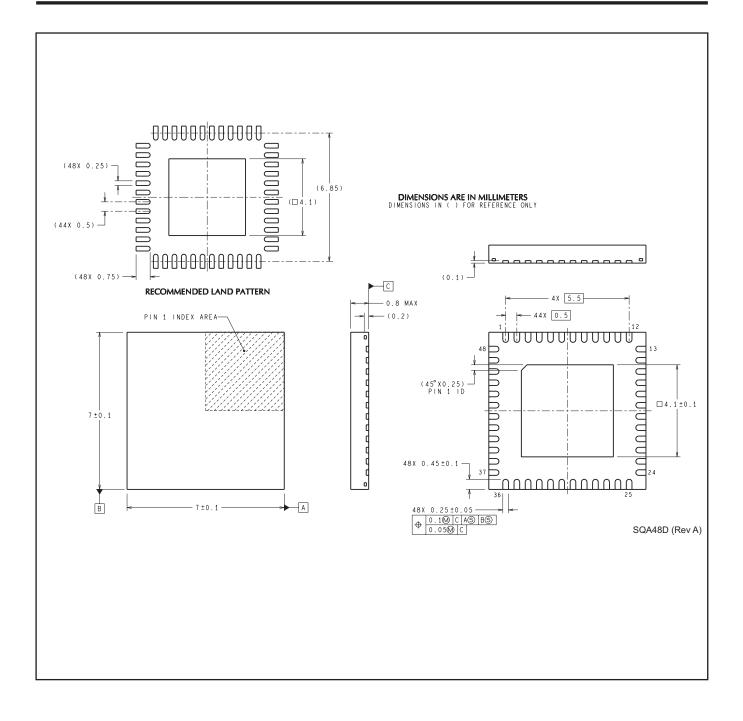


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS64EV400SQ/NOPB	WQFN	NJU	48	250	213.0	191.0	55.0
DS64EV400SQX/NOPB	WQFN	NJU	48	2500	367.0	367.0	38.0

# **MECHANICAL DATA**

# NJU0048D





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